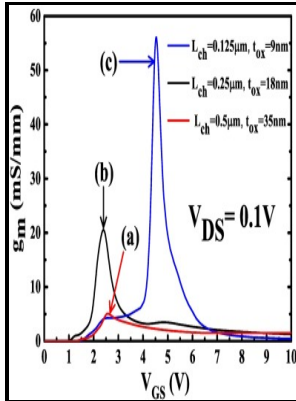


# Lateral superjunction power MOSFETs.

National Library of Canada - MDmesh: 20 Years of Superjunction STPOWER™ MOSFETs, A Story About Innovation



Description: -

-Lateral superjunction power MOSFETs.

-

Canadian theses = -- Thèses canadiennes Lateral superjunction power MOSFETs.

Notes: Thesis (M.A.Sc.) -- University of Toronto, 2001.

This edition was published in 2001



Filesize: 34.53 MB

Tags: #US6787872B2

## Extended Trench Gate Superjunction Lateral Power MOSFET for Ultra

Typical discrete transistors include power MOSFETs and IGBTs Insulated Gate Bipolar Transistors.

## Exicon Lateral MOSFETS

Then, as shown in FIG.

## Figure 4 from Superjunction Power Devices, History, Development, and Future Prospects

Unlike the conventional SJ structure, a thin oxide layer is formed in between the p-n columns to avoid the p-n column interdiffusion Gan et al. Figure 3 compares the electric field in the drift region vs.

## Figure 4 from Superjunction Power Devices, History, Development, and Future Prospects

The mesa width, that is, the space between trenches, may be about 1. Planar MOSFETs typically have a high drain-to-source resistance per unit of silicon area, and come with relatively higher drain source resistances.

---

## Related Books

- [Bully in your relationship - stand up to emotional abuse and get the love you deserve](#)
- [SLA and the literature classroom - fostering dialogues](#)
- [17. Juni 1953 - Bibliographie](#)
- [Storia e metodi della psicologia del lavoro](#)
- [Magnets & batteries](#)